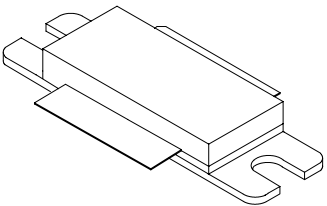




1011LD200

200 Watts, 32 Volts

Pulsed Avionics 1030 to 1090 MHz
LDMOS FET

| | |
|---|--|
| <p>GENERAL DESCRIPTION</p> <p>The 1011LD200 is a COMMON SOURCE N-Channel enhancement mode lateral MOSFET capable of providing 200 W_{pk} of RF power from 1030 to 1090 MHz. The device is nitride passivated and utilizes gold metallization to ensure highest MTTF. The transistor includes input prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.</p> | <p>CASE OUTLINE 55QX-1 (Common Source)</p>  |
| <p>ABSOLUTE MAXIMUM RATINGS</p> <p>Power Dissipation Device Dissipation @25°C (P_d) 700 W</p> <p>Voltage and Current Drain-Source (V_{DSS}) 75V Gate-Source (V_{GS}) ± 20V</p> <p>Temperatures Storage Temperature -65 to +150°C Operating Junction Temperature +200°C</p> | |

ELECTRICAL CHARACTERISTICS @ 25°C

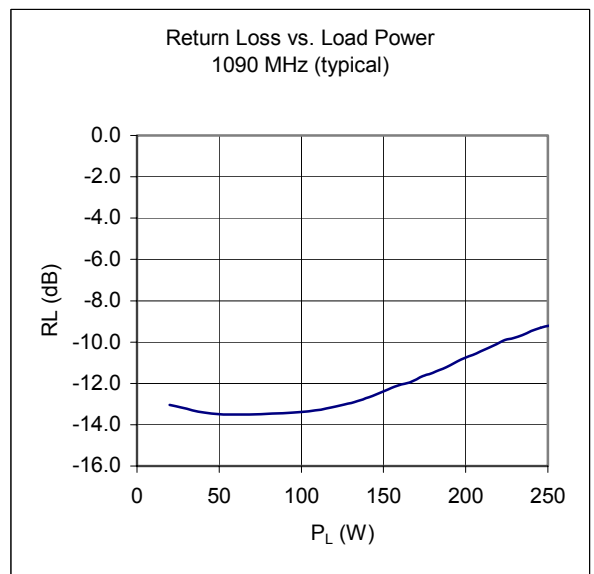
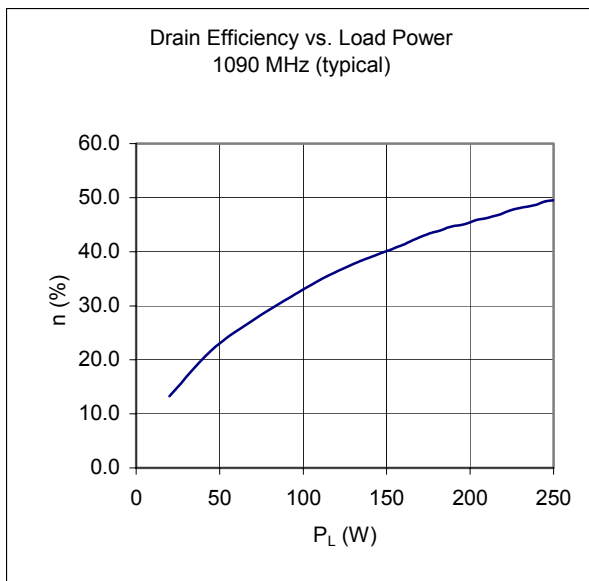
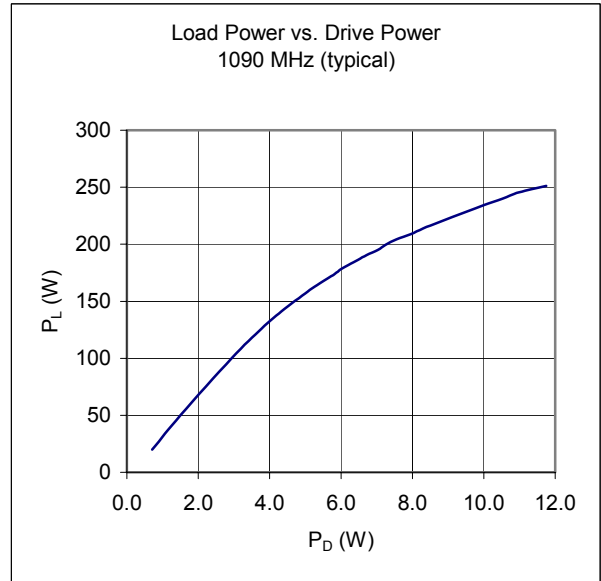
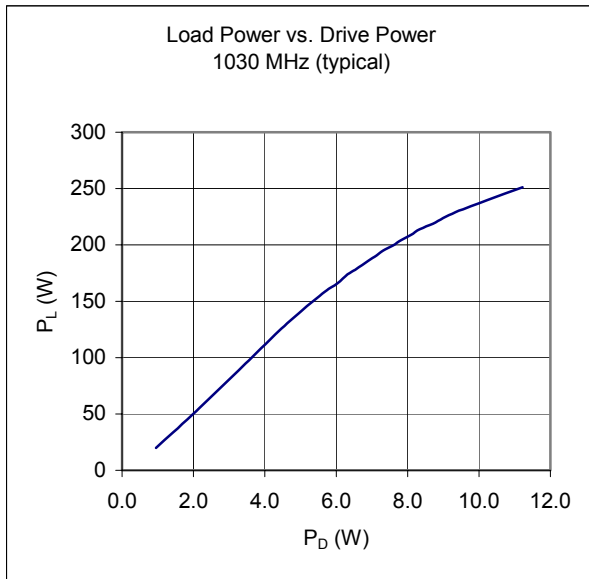
| SYMBOL | CHARACTERISTICS | TEST CONDITIONS | MIN | TYP | MAX | UNITS |
|------------------------------|------------------------------|---|-----|-----|------|-------|
| BV _{dss} | Drain-Source Breakdown | V _{gs} = 0V, I _d = 20mA | 75 | | | V |
| I _{dss} | Drain-Source Leakage Current | V _{ds} = 38V, V _{gs} = 0V | | | 10 | μA |
| I _{gss} | Gate-Source Leakage Current | V _{gs} = 10V, V _{ds} = 0V | | | 1 | μA |
| V _{gs(th)} | Gate Threshold Voltage | V _{ds} = 10V, I _d = 40 mA | 3 | | 6 | V |
| V _{ds(on)} | Drain-Source On Voltage | V _{gs} = 10V, I _d = 2A | | | 0.3 | V |
| g _{FS} | Forward Transconductance | V _{ds} = 10V, I _d = 2A | | 2 | | S |
| θ _{JC} ¹ | Thermal Resistance | | | | 0.25 | °C/W |

FUNCTIONAL CHARACTERISTICS @ 25°C, V_{ds} = 32V, I_{dq} = 500mA

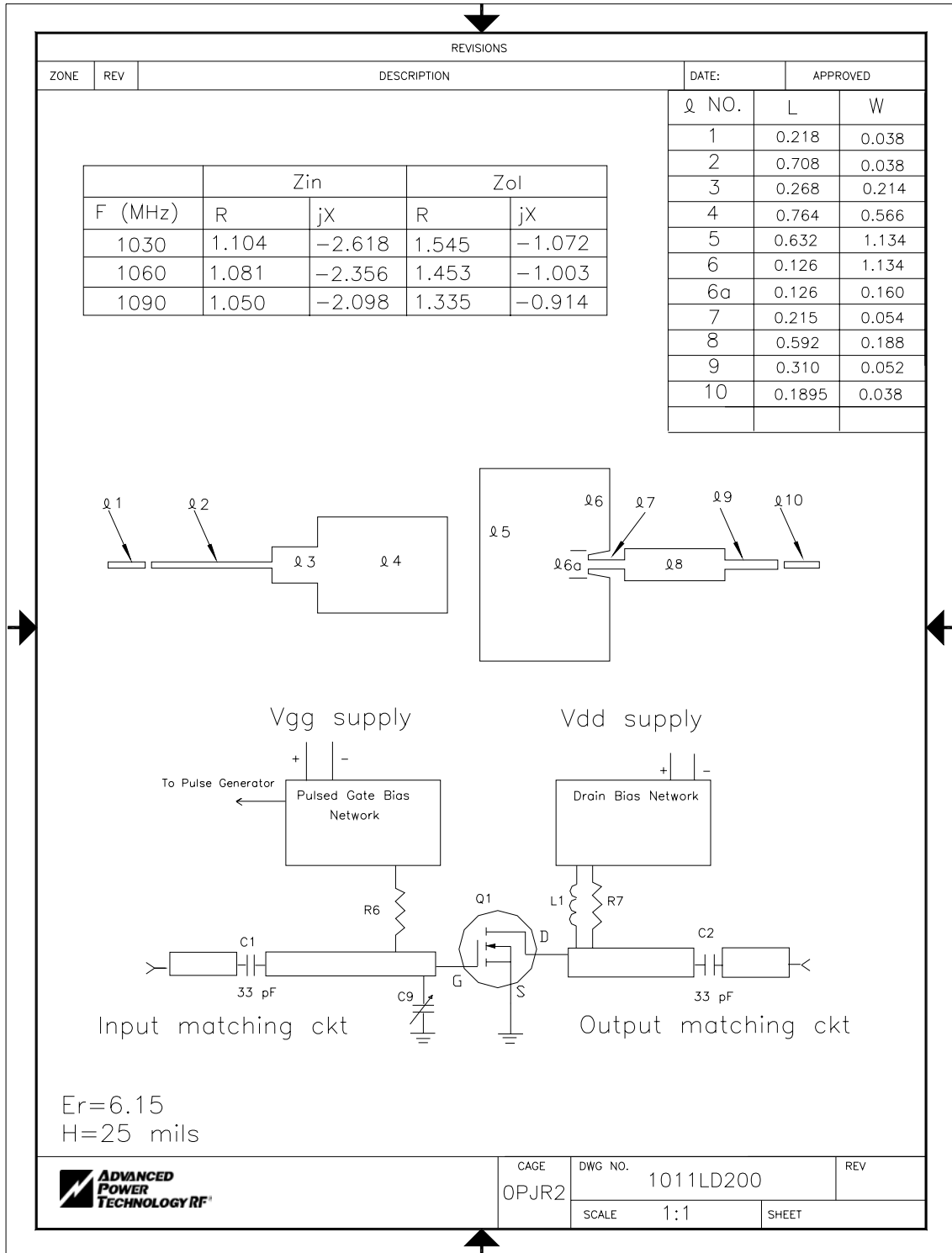
| | | | | | | |
|-----------------|--------------------------|--|----|----|-----|----|
| G _{PS} | Common Source Power Gain | Pulse width = 32 μs, LTDC=2% | 13 | 15 | | dB |
| P _d | Pulse Droop | F=1030/1090 MHz, P _{out} = 200W | | | 0.5 | dB |
| η _d | Drain Efficiency | F = 1030 MHz, P _{out} = 200W | 43 | | | % |
| ψ | Load Mismatch | F = 1090 MHz, P _{out} = 200W | | | 3:1 | |

NOTES: 1. At rated output power and pulse conditions

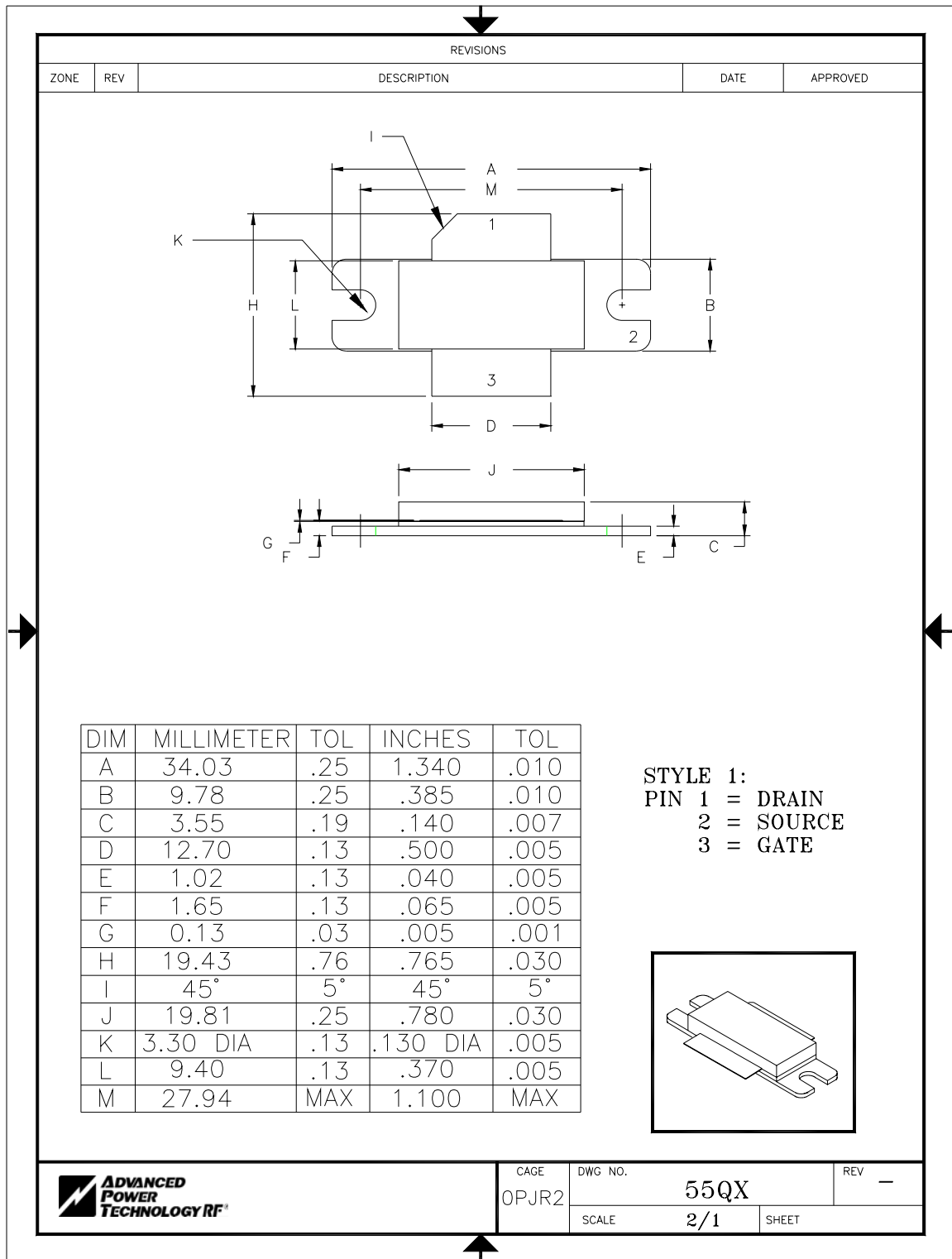
Rev. B - Apr 2004



1011LD200



1011LD200



This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.